# **General Purpose Transistor**

# **PNP Silicon**

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-416/SC-75 which is designed for low power surface mount applications.

### **Features**

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device



Rating	Symbol	Max	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	-45	V
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current – Continuous	Ic	-100	mAdc
Collector Current – Peak	Ic	-200	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1) T <sub>A</sub> = 25°C Derated above 25°C	P <sub>D</sub>	200 1.6	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ heta JA}$	600	°C/W
Total Device Dissipation, FR-4 Board (Note 2) T <sub>A</sub> = 25°C Derated above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	400	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

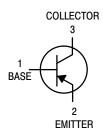
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-4 @ min pad.
- 2. FR-4 @ 1.0 × 1.0 in pad.



## ON Semiconductor®

### http://onsemi.com





CASE 463 SOT-416 STYLE 1

### **MARKING DIAGRAM**



3F = Device Code

M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•				
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = -10 mA)	V <sub>(BR)CEO</sub>	-45	-	-	V
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = -10 µA, V <sub>EB</sub> = 0)	V <sub>(BR)CES</sub>	-50	-	-	V
Collector – Base Breakdown Voltage (I <sub>C</sub> = –10 μA)	V <sub>(BR)CBO</sub>	-50	-	-	V
Emitter – Base Breakdown Voltage (I <sub>E</sub> = –1.0 μA)	V <sub>(BR)EBO</sub>	-5.0	_	-	V
Collector Cutoff Current ( $V_{CB} = -30 \text{ V}$ ) ( $V_{CB} = -30 \text{ V}$ , $T_A = 150^{\circ}\text{C}$ )	I <sub>CBO</sub>	-	_ _	-15 -4.0	nA μA
ON CHARACTERISTICS	·				
DC Current Gain $(I_C = -10 \mu A, V_{CE} = -5.0 \text{ V})$ $(I_C = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V})$	h <sub>FE</sub>	- 220	150 290	- 475	-
Collector – Emitter Saturation Voltage ( $I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$ ) ( $I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA}$ )	V <sub>CE(sat)</sub>	- -	_ _	-0.3 -0.65	V
Base – Emitter Saturation Voltage ( $I_C$ = -10 mA, $I_B$ = -0.5 mA) ( $I_C$ = -100 mA, $I_B$ = -5.0 mA)	V <sub>BE(sat)</sub>	- -	-0.7 -0.9	- -	V
Base – Emitter On Voltage ( $I_C = -2.0$ mA, $V_{CE} = -5.0$ V) ( $I_C = -10$ mA, $V_{CE} = -5.0$ V)	V <sub>BE(on)</sub>	-0.6 -	_ _	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I <sub>C</sub> = –10 mA, V <sub>CE</sub> = –5.0 Vdc, f = 100 MHz)	f <sub>T</sub>	100	_	_	MHz
Output Capacitance (V <sub>CB</sub> = -10 V, f = 1.0 MHz)	C <sub>ob</sub>	-	-	4.5	pF
Noise Figure $ \text{(I}_{\text{C}} = -0.2 \text{ mA, V}_{\text{CE}} = -5.0 \text{ Vdc, R}_{\text{S}} = 2.0 \text{ k}\Omega, \\ \text{f} = 1.0 \text{ kHz, BW} = 200 \text{ Hz)} $	NF	-	_	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### **TYPICAL CHARACTERISTICS**

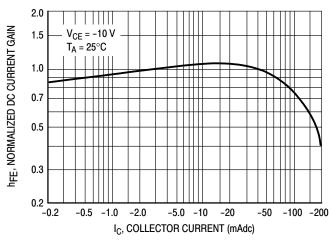


Figure 1. Normalized DC Current Gain

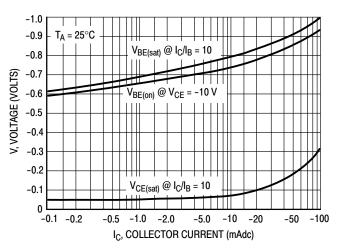


Figure 2. "Saturation" and "On" Voltages

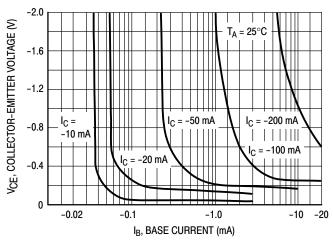


Figure 3. Collector Saturation Region

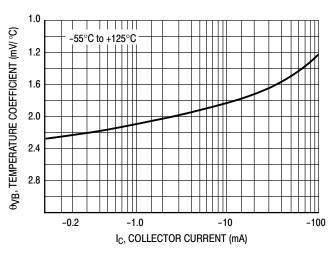


Figure 4. Base-Emitter Temperature Coefficient

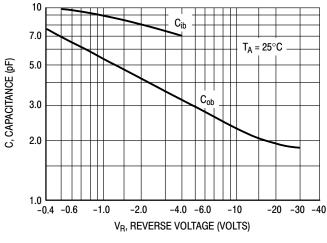


Figure 5. Capacitances

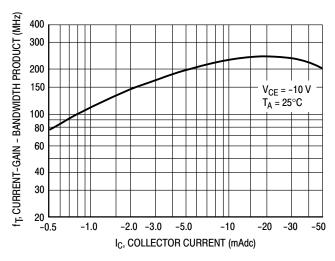


Figure 6. Current-Gain - Bandwidth Product

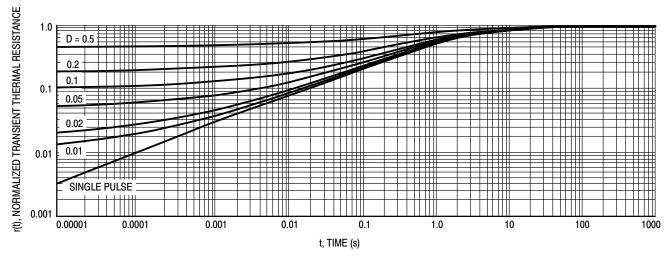


Figure 7. Thermal Response

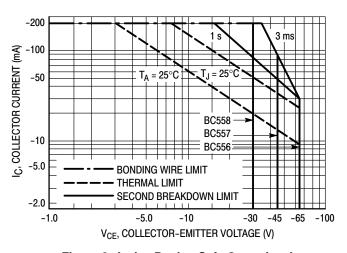


Figure 8. Active Region Safe Operating Area

The safe operating area curves indicate  $I_C$ – $V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 8 is based upon  $T_{J(pk)} = 150^{\circ}C$ ;  $T_{C}$  or  $T_{A}$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 7. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>	
BC857BTT1G	SOT-416	2 000 / Tong & Real	
NSVBC857BTT1G*	(PB-Free)	3,000 / Tape & Reel	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

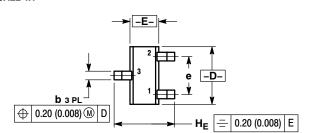
<sup>\*</sup>NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

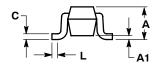




SC-75/SOT-416 **CASE 463** ISSUE G

**DATE 07 AUG 2015** 





STYLE 1: PIN 1. BASE 2. EMITTER STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. COLLECTOR 3. CATHODE STYLE 4: STYLE 5: PIN 1. CATHODE 2. CATHODE PIN 1. GATE 2. SOURCE

3. DRAIN

## **GENERIC MARKING DIAGRAM\***

3. ANODE



XX = Specific Device Code Μ = Date Code

= Pb-Free Package

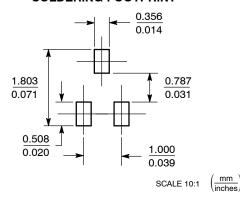
\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
E	0.70	0.80	0.90	0.027	0.031	0.035
е	1.00 BSC				0.04 BSC	)
L	0.10	0.15	0.20	0.004	0.006	0.008
He	1.50	1.60	1.70	0.060	0.063	0.067

### RECOMMENDED **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98ASB15184C	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SC-75/SOT-416		PAGE 1 OF 1	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales